

HIGH SELECTIVITY SiC ETCH IN INTEGRATED CIRCUIT FABRICATION

Abstract

The subject matter described herein involves an improved etch process for use in fabricating integrated circuits on semiconductor wafers. The selectivity of the etch process for silicon carbide versus silicon oxide, organo silica-glass or other low dielectric constant type material is enhanced by adding hydrogen (H₂) or ammonia (NH₃) or other hydrogen-containing gas to the etch chemistry.